TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA541FK

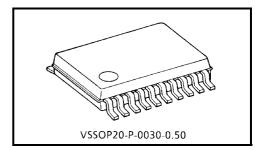
Low-Voltage Octal Bus Buffer with 3.6 V Tolerant Inputs and Outputs

The TC7MA541FK is a high performance CMOS octal bus buffer. Designed for use in 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaing the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6\,\mathrm{V}.$

The device is a non-inverting 3-state buffer having two active-low output enables. When either $\overline{OE}1$ or $\overline{OE}2$ are high, the terminal outputs are in the high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.03 g (typ.)

Features

- Low voltage operation: $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High speed operation: $t_{pd} = 3.5 \text{ ns (max) (VCC} = 3.0 \sim 3.6 \text{ V)}$

 $t_{pd} = 4.2 \text{ ns (max) (V}_{CC} = 2.3 \sim 2.7 \text{ V})$

 $t_{pd} = 8.4 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $I_{OH}/I_{OL} = \pm 18 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

 $IOH/IOL = \pm 6 \text{ mA (min) (VCC} = 1.8 \text{ V)}$

- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

Human body model $> \pm 2000 \text{ V}$

- Package: VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)
 - *: To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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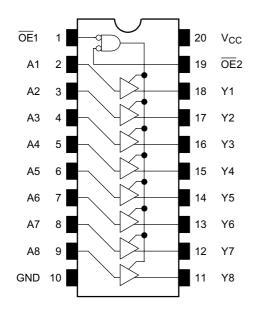
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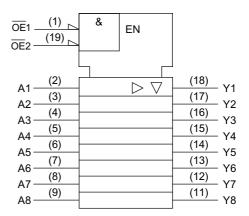
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Pin Assignment (top view)

TOSHIBA



IEC Logic Level



Truth Table

	Inputs						
OE1	OE2	An	Outputs				
Н	Х	Х	Z				
Х	Н	Х	Z				
L	L	Н	Н				
L	L	L	L				

X: Don't care

Z: High impedance

Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~4.6	V
DC input voltage	V _{IN}	-0.5~4.6	V
		-0.5~4.6 (Note 1)	
DC output voltage	Vout	-0.5~V _{CC} + 0.5 (Note 2)	V
Input diode current	I _{IK}	-50	mA
Output diode current	lok	±50 (Note 3)	mA
DC output current	lout	±50	mA
Power dissipation	PD	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65~150	°C

Note 1: Off-state

Note 2: High or low state. IOUT absolute maximum rating must be observed.

Note 3: V_{OUT} < GND, V_{OUT} > V_{CC}



Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	1.8~3.6	V
Supply voltage	VCC	1.2~3.6 (Note 4)	V
Input voltage	V _{IN}	-0.3~3.6	٧
Output voltage	Vout	0~3.6 (Note 5)	· V
Output voltage	VOU1	0~V _{CC} (Note 6)	V
		±24 (Note 7)	
Output current	I _{OH} /I _{OL}	±18 (Note 8)	mA
		±6 (Note 9)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 10)	ns/V

Note 4: Data retention only

Note 5: Off-state

Note 6: High or low state

Note 7: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note 8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 9: $V_{CC} = 1.8 \text{ V}$

Note 10: $V_{IN} = 0.8 \sim 2.0 \text{ V}$, $V_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} \leq 3.6 V)

Characteristics		Symbol	Test Condition			Min	Max	Unit
Characte	HSUCS	Syllibol	Tes	t Condition	V _{CC} (V)	IVIIII	IVIAX	Offic
Input voltage	High level	V_{IH}		_	2.7~3.6	2.0	_	V
iliput voltage	Low level	V _{IL}		_	2.7~3.6	_	0.8	v
				$I_{OH} = -100 \mu A$	2.7~3.6	V _{CC} - 0.2	_	
	High level	Voh	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -12 \text{ mA}$	2.7	2.2	_	
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_	
Output voltage				$I_{OH} = -24 \text{ mA}$	3.0	2.2	_	V
			$I_{OL} = 100 \mu A$	2.7~3.6	_	0.2		
	Low level	VOI	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 12 mA	2.7	_	0.4	
	Low level	VOL		I _{OL} = 18 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μА
2 state output off o	otata aurrant	1	$V_{IN} = V_{IH}$ or V_{IL}		2.7~3.6		±10.0	
3-state output off-state current		loz	V _{OUT} = 0~3.6 V		2.1~3.0	_	±10.0	μΑ
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА
Quiescent supply current		loo	V _{IN} = V _{CC} or GND		2.7~3.6	_	20.0	
		Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le$	3.6 V	2.7~3.6	_	±20.0	μΑ
		Δl _{CC}	$V_{IH} = V_{CC} - 0.6 V$ (pe	er input)	2.7~3.6	_	750	



DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteristics		Symbol	Tes	st Condition		Min	Max	Unit	
		•			V _{CC} (V)				
Input voltage	High level	VIH		_	2.3~2.7	1.6	_	V	
input voltage	Low level	V _{IL}		_	2.3~2.7	_	0.7	V	
				$I_{OH} = -100 \mu A$	2.3~2.7	V _{CC} - 0.2	_		
	High level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -6 \text{ mA}$	2.3	2.0	_		
				I _{OH} = -12 mA	2.3	1.8	_	V	
Output voltage				$I_{OH} = -18 \text{ mA}$	2.3	1.7	_		
			$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	2.3~2.7	_	0.2		
	Low level	V _{OL}		$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 12 \text{ mA}$	2.3	_	0.4	
					$I_{OL} = 18 \text{ mA}$	2.3	_	0.6	
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	_	±5.0	μΑ	
3-state output off-state current		la-	$V_{IN} = V_{IH}$ or V_{IL}		2.3~2.7		±10.0		
		loz	V _{OUT} = 0~3.6 V		2.3~2.1		±10.0	μΑ	
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0		10.0	μΑ	
Quiescent supply	Outros and supply supply		V _{IN} = V _{CC} or GND		2.3~2.7	_	20.0		
Quiescent supply	oun c nt	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le$	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		_	±20.0	μА	

DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteri	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit				
Input voltage	High level	V _{IH}	-		1.8~2.3	0.7× V _{CC}	_	V				
input voitage	Low level	V _{IL}	-	_	1.8~2.3	_	0.2× V _{CC}	V				
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_					
Output voltage				$I_{OH} = -6 \text{ mA}$	1.8	1.4	_	V				
	Low level	V/	\\ = \\ or \\	I _{OL} = 100 μA	1.8	_	0.2					
	Low level	V_{OL} $V_{IN} = V_{IH}$ or V_{IL}	VIN — VIH OI VIL	I _{OL} = 6 mA	1.8	_	0.3					
Input leakage curre	nt	I _{IN}	V _{IN} = 0~3.6 V		1.8	_	±5.0	μΑ				
3-state output off-st	ate current	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8	_	±10.0	μА				
Power off leakage of	urrent	loff	V _{IN} , V _{OUT} = 0~3.6 V		V _{IN} , V _{OUT} = 0~3.6 V		V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
Quiescent supply current		Icc	$V_{IN} = V_{CC}$ or GND	V _{IN} = V _{CC} or GND			20.0	μА				
Quiescent supply co	ni Giit	icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6$	6 V	1.8	_	±20.0	μΑ				



AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	Min	Max	Unit
			V _{CC} (V)	4.5	0.4	
Dranagation dalay time	t _{pLH}	Figure 1 Figure 2	1.8	1.5	8.4	no
Propagation delay time	t _{pHL}	Figure 1, Figure 2	2.5 ± 0.2	8.0	4.2	ns
	-		3.3 ± 0.3	0.6	3.5	
	4		1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	8.0	5.5	ns
			3.3 ± 0.3	0.6	4.5	
			1.8	1.5	6.5	
3-state output disable time		t _{pLZ} Figure 1, Figure 3	2.5 ± 0.2	8.0	3.6	ns
	t _{pHZ}		3.3 ± 0.3	0.6	3.3	
+ .			1.8		0.5	
Output to output skew	tosLH	(Note 11)	2.5 ± 0.2		0.5	ns
	t _{osHL}		3.3 ± 0.3	_	0.5	

For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 11: This parameter is guaranteed by design.

 $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition		V _{CC} (V)	Тур.	Unit
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	te 12)	1.8	0.25	
Quiet output maximum dynamic V _{OL}	V_{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	te 12)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	te 12)	3.3	8.0	
	V _{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	te 12)	1.8	-0.25	V
Quiet output minimum dynamic V _{OL}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	te 12)	2.5	-0.6	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	te 12)	3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	te 12)	1.8	1.5	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	te 12)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	te 12)	3.3	2.2	

Note 12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Cumphal	Test Condition			T. m	Unit
Characteristics	Symbol			V _{CC} (V)	Тур.	Unit
Input capacitance	C _{IN}	_		1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (No	ote 13)	1.8, 2.5, 3.3	20	pF

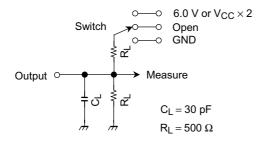
Note 13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$



AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	6.0 V V _{CC} × 2	$@V_{CC} = 3.3 \pm 0.3 \text{ V}$ $@V_{CC} = 2.5 \pm 0.2 \text{ V}$ $@V_{CC} = 1.8 \text{ V}$	
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

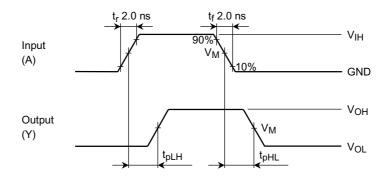


Figure 2 t_{pLH}, t_{pHL}

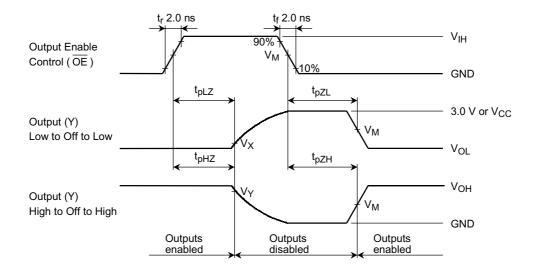
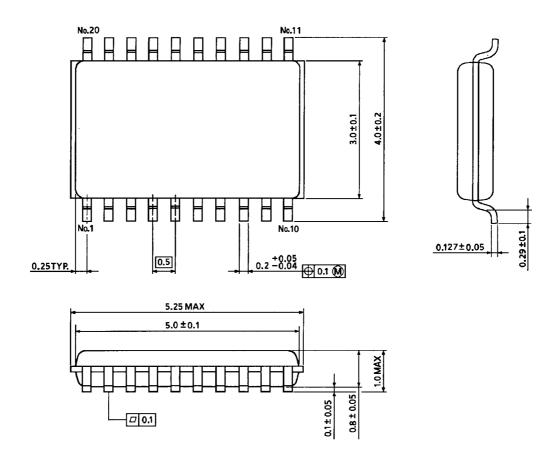


Figure 3 $t_{pLZ},\,t_{pHZ},\,t_{pZL},\,t_{pZH}$

Cumbal		V _{CC}	
Symbol	$3.3 \pm 0.3 \text{ V}$	2.5 ± 0.2 V	1.8 V
V _{IH}	2.7 V	V _{CC}	V _{CC}
V_{M}	1.5 V	V _{CC} /2	V _{CC} /2
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

Package Dimensions



Weight: 0.03 g (typ.)